Supporting Information

High Growth Rate and High Wet Etch Resistance Silicon Nitride Grown by Low Temperature Plasma Enhanced Atomic Layer Deposition with a Novel Silylamine Precursor

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Fig. S1 Tabulated values for the errors in GPC, R.I., and WER. (a) GPC and R.I., and their error values in Fig. 3a. (b) GPC, R.I. and WER, and their error values in Fig. 3b, Fig. 3c, and Fig. 5, respectively.
Fig. S2 XPS spectra acquired after removing ~2 nm of air-oxidized top layer by 1 min of Ar⁺ sputtering. The spectra are taken from PEALD SiNₓ using TDSA with N₂ HCP at a power of 100 W with process temperatures of 240 °C, 270 °C, 300 °C, and 360 °C.
Fig. S3 XRR spectra acquired from PEALD SiN$_x$ using TDSA with N$_2$ HCP at a power of 100 W with process temperatures of 240 °C, 270 °C, 300 °C, and 360 °C (black lines). Red lines are simulated results to fit measurement data. Inserted tabulated data are the parameters extracted from the calculation results.
Fig. S4. FT-IR analyses for PEALD SiN\textsubscript{x} using TDSA with N\textsubscript{2} HCP at a power of 100 W with process temperatures of 270 °C, 300 °C, and 360 °C. Note changes in –NSiH\textsubscript{3} stretching mode with temperatures. This indicates TDSA tends to react with the surface by dissociating the N–Si bond in the N–SiH\textsubscript{2}SiH\textsubscript{3} groups of TDSA, making films more Si rich instead of liberating only –SiH\textsubscript{3} at a higher temperature.

Thermo Electron FT-IR spectroscopy operating with a Globar IR source and liquid-nitrogen-cooled MCT-A infrared detector is used to perform the vibrational spectroscopic studies. The infrared beam passes through a KBr beam splitter. Spectra are obtained in absorbance mode. For each sample, background spectra are acquired using a silicon piece cleaved from the same wafer on which the deposited silicon nitride film is etched away using DHF (49% HF:H\textsubscript{2}O = 1:100). The IR data generated from the deposited SiN\textsubscript{x} films on silicon substrates are collected with a spectral resolution of 4 cm\textsuperscript{-1} over 100 scans. The background spectra generated from the cleaved piece of silicon are collected with a resolution of 4 cm\textsuperscript{-1} as well. The spectrometer is purged with N\textsubscript{2} prior to the measurement to minimize the presence of trapped water in the IR beamline.